

# LME49860 44V Dual High Performance, High Fidelity Audio Operational Amplifier

## **General Description**

The LME49860 is part of the ultra-low distortion, low noise, high slew rate operational amplifier series optimized and fully specified for high performance, high fidelity applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LME49860 audio operational amplifiers deliver superior audio signal amplification for outstanding audio performance. The LME49860 combines extremely low voltage noise density (2.7nV/ $\sqrt{Hz}$ ) with vanishingly low THD+N (0.00003%) to easily satisfy the most demanding audio applications. To ensure that the most challenging loads are driven without compromise, the LME49860 has a high slew rate of ±20V/µs and an output current capability of ±26mA. Further, dynamic range is maximized by an output stage that drives  $2k\Omega$  loads to within 1V of either power supply voltage and to within 1.4V when driving 600 $\Omega$  loads.

The LME49860's outstanding CMRR (120dB), PSRR (120dB), and  $V_{OS}$  (0.1mV) give the amplifier excellent operational amplifier DC performance.

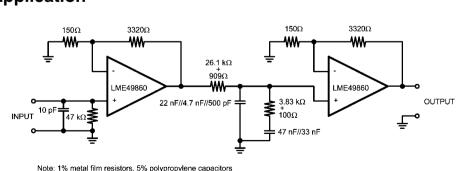
The LME49860 has a wide supply range of  $\pm 2.5V$  to  $\pm 22V$ . Over this supply range the LME49860 maintains excellent common-mode rejection, power supply rejection, and low input bias current. The LME49860 is unity gain stable. This Audio Operational Amplifier achieves outstanding AC performance while driving complex loads with values as high as 100pF.

The LME49860 is available in 8–lead narrow body SOIC and 8–lead Plastic DIP packages. Demonstration boards are available for each package.

# **Key Specifications**

- Power Supply Voltage Range
- THD+N
  - $(A_V = 1, V_{OUT} = 3V_{BMS}, f_{IN} = 1kHz)$

# **Typical Application**



±2.5V to ±22V

Passively Equalized RIAA Phono Preamplifier

$R_L = 2k\Omega$	0.00003% (typ)
R <sub>L</sub> = 600Ω	0.00003% (typ)
Input Noise Density	2.7nV/ $√$ Hz (typ)
Slew Rate	±20V/μs (typ)
Gain Bandwidth Product	55MHz (typ)
Open Loop Gain ( $R_L = 600\Omega$ )	140dB (typ)
Input Bias Current	10nA (typ)
Input Offset Voltage	0.1mV (typ)

DC Gain Linearity Error 0.000009%

## **Features**

- Easily drives 600Ω loads
- Optimized for superior audio signal fidelity
- Output short circuit protection
- PSRR and CMRR exceed 120dB (typ)
- SOIC, DIP packages

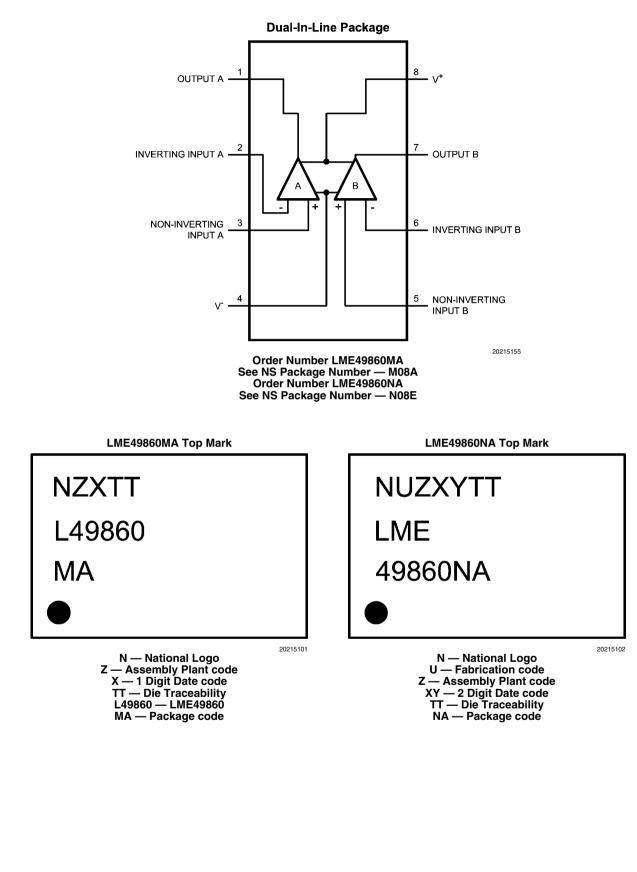
## Applications

- Ultra high quality audio amplification
- High fidelity preamplifiers
- High fidelity multimedia
- State of the art phono pre amps
- High performance professional audio
- High fidelity equalization and crossover networks
- High performance line drivers
- High performance line receivers
- High fidelity active filters

202151k5



## **Connection Diagrams**



## Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Power Supply Voltage	
$(V_{S} = V^{+} - V^{-})$	46V
Storage Temperature	–65°C to 150°C
Input Voltage	(V-) - 0.7V to (V+) + 0.7V
Output Short Circuit (Note 3)	Continuous
ESD Susceptibility (Note 4)	2000V
ESD Susceptibility (Note 5)	
Pins 1, 4, 7 and 8	200V

Pins 2, 3, 5 and 6 Junction Temperature Thermal Resistance  $\theta_{IA}$  (SO) 145°C/W  $\theta_{JA}$  (NA) 102°C/W

**Operating Ratings** 

Temperature Range

$T_{MIN} \le T_A \le T_{MAX}$	-
Supply Voltage Range	±

 $-40^{\circ}C \le T_A \le 85^{\circ}C$  $\pm 2.5V \le V_S \le \pm 22V$ 

Electrical Characteristics for the LME49860 (Note 1) The following specifications apply for  $V_s =$ ±18V and ±22V,  $R_L = 2k\Omega$ ,  $R_{SOURCE} = 10\Omega$ ,  $f_{IN} = 1$ kHz,  $T_A = 25^{\circ}$ C, unless otherwise specified.

			LME	LME49860	
Symbol	Parameter	Conditions	Typical	Typical Limit	
			(Note 6)	(Note 7)	(Limits)
		$A_V = 1, V_{OUT} = 3V_{rms}$			
THD+N	Total Harmonic Distortion + Noise	$R_{L} = 2k\Omega$	0.00003		% (max)
		$R_{L} = 600\Omega$	0.00003	0.00009	
IMD	Intermodulation Distortion	A <sub>V</sub> = 1, V <sub>OUT</sub> = 3V <sub>RMS</sub> Two-tone, 60Hz & 7kHz 4:1	0.00005		%
GBWP	Gain Bandwidth Product		55	45	MHz (min
SR	Slew Rate		±20	±15	V/µs (min
FPBW	Full Power Bandwidth	$V_{OUT} = 1V_{P-P}$ , -3dB referenced to output magnitude at f = 1kHz	10		MHz
t <sub>s</sub>	Settling time	A <sub>V</sub> = -1, 10V step, C <sub>L</sub> = 100pF 0.1% error range	1.2		μs
0	Equivalent Input Noise Voltage	f <sub>BW</sub> = 20Hz to 20kHz	0.34	0.65	μV <sub>RMS</sub> (max)
e <sub>n</sub>	Equivalent Input Noise Density	f = 1kHz	2.7	4.7	nV/√Hz
	Equivalent Input Noise Density	f = 10Hz	6.4		(max)
i <sub>n</sub>	Current Noise Density	f = 1kHz	1.6		p <b>A/</b> √Hz
		f = 10Hz	3.1		
V <sub>os</sub>	Offset Voltage	$V_{S} = \pm 18V$	±0.12	±0.7	mV (max)
- 05		V <sub>S</sub> = ±22V	±0.14	±0.7	mV (max)
ΔV <sub>OS</sub> /ΔTemp	Average Input Offset Voltage Drift vs Temperature	–40°C ≤ T <sub>A</sub> ≤ 85°C	0.2		μV/°C
	Average Input Offset Voltage Shift vs	(Note 8)			
PSRR	Power Supply Voltage	$V_{\rm S} = \pm 18$ V, $\Delta V_{\rm S} = 24$ V	120		dB
		$V_{\rm S} = \pm 22 \text{V}, \Delta V_{\rm S} = 30 \text{V}$	120	110	dB (min)
ISO <sub>CH-CH</sub>	Channel-to-Channel Isolation	f <sub>IN</sub> = 1kHz f <sub>IN</sub> = 20kHz	118 112		dB
I <sub>B</sub>	Input Bias Current	$V_{CM} = 0V$	10	72	nA (max)
ΔI <sub>OS</sub> /ΔTemp	Input Bias Current Drift vs Temperature	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le 85^{\circ}\text{C}$	0.1		nA/°C
I <sub>os</sub>	Input Offset Current	V <sub>CM</sub> = 0V	11	65	nA (max)
		$V_{\rm S} = \pm 18 V$	+17.1	(V+) – 2.0	V (min)
V			-16.9	(V-) + 2.0	V (min)
V <sub>IN-CM</sub>	Common-Mode Input Voltage Range	$V_{\rm S} = \pm 22V$	+21.0	(V+) – 2.0	V (min)
			-20.8	(V-) + 2.0	V (min)

LME49860

100V

150°C

			LME4	LME49860	
Symbol	Parameter	Conditions	Typical	1	
			(Note 6)	(Note 7)	(Limits)
		V <sub>S</sub> = ±18V	400		
		$-12V \le V_{CM} \le 12V$	120		dB
CMRR	Common-Mode Rejection	$V_{\rm S} = \pm 22 V$			
		-15V ≤ V <sub>CM</sub> ≤ 15V	120	110	dB (mir
_	Differential Input Impedance		30		kΩ
Z <sub>IN</sub>	Common Mode Input Impedance	-10V <vcm<10v< td=""><td>1000</td><td></td><td>MΩ</td></vcm<10v<>	1000		MΩ
		$V_{\rm S} = \pm 18 V$			
		$R_{L} = 600\Omega$	140		dB
		$R_{L} = 2k\Omega$	140		dB
		$R_{L} = 10k\Omega$	140		dB
A <sub>VOL</sub>	Open Loop Voltage Gain	$V_{\rm S} = \pm 22V$			
		_15V≤Vout≤15V			
		$R_{L} = 600\Omega$	140	125	dB (mir
		$R_{L} = 2k\Omega$	140		dB (min
		$R_{L} = 10k\Omega$	140		dB
		R <sub>L</sub> = 600Ω			
		$V_{\rm S} = \pm 18 V$	±16.7		v v
		$V_{S} = \pm 22V$	±20.4	±19.0	V (min
		$R_L = 2k\Omega$			
V <sub>OUTMAX</sub>	Maximum Output Voltage Swing	$V_{\rm S} = \pm 18 V$	±17.0		v V
		$V_{S} = \pm 22V$	±21.0		V
		$R_L = 10k\Omega$			
		$V_{S} = \pm 18V$	±17.1		v v
		V <sub>S</sub> = ±22V	±21.2		V
		R <sub>L</sub> = 600Ω			
l <sub>out</sub> Ou	Output Current	$V_{\rm S} = \pm 20 V$	±31		mA
		V <sub>S</sub> = ±22V	±37	±30	mA (mii
I <sub>OUT-CC</sub>	Instantaneous Short Circuit Current		+53		mA
001-00			-42		
D	Output Impedance	f <sub>IN</sub> = 10kHz	0.01		
R <sub>OUT</sub>	Output Impedance	Closed-Loop Open-Loop	0.01 13		Ω
C <sub>LOAD</sub>	Capacitive Load Drive Overshoot	100pF	16		%
LUAD		$I_{OUT} = 0 \text{mA}$	10		/0
I <sub>s</sub>	Total Quiescent Current	$V_{\rm S} = \pm 18V$	10.2		mA
3		$V_{\rm S} = \pm 22V$	10.2	13	mA (ma

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.

**Note 2:** Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 3: Amplifier output connected to GND, any number of amplifiers within a package.

Note 4: Human body model, 100pF discharged through a  $1.5 k\Omega$  resistor.

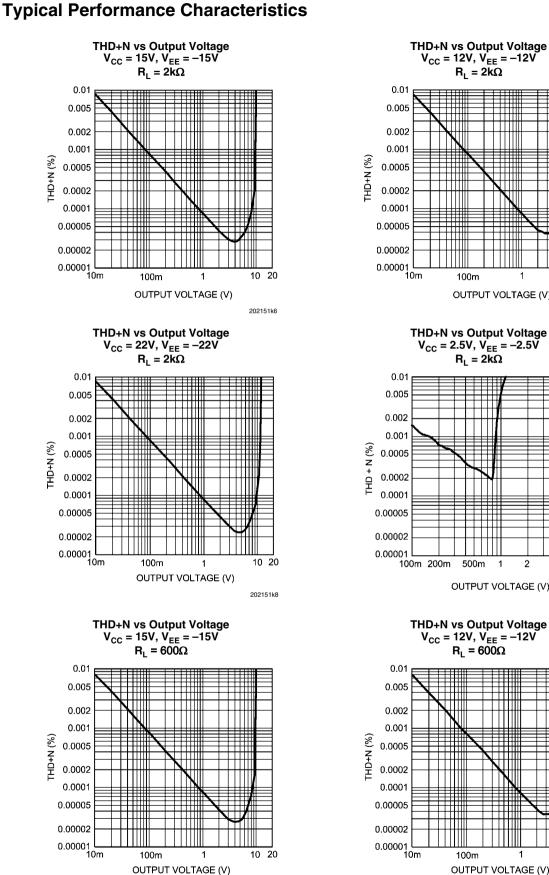
Note 5: Machine Model ESD test is covered by specification EIAJ IC-121-1981. A 200pF cap is charged to the specified voltage and then discharged directly into the IC with no external series resistor (resistance of discharge path must be under  $50\Omega$ ).

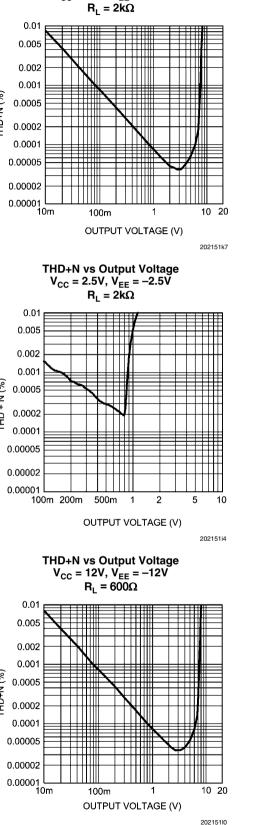
Note 6: Typical specifications are specified at +25°C and represent the most likely parametric norm.

Note 7: Tested limits are guaranteed to National's AOQL (Average Outgoing Quality Level).

Note 8: PSRR is measured as follows: For V<sub>S</sub> = ±22V, V<sub>OS</sub> is measured at two supply voltages, ±7V and ±22V. PSRR = |  $20log(\Delta V_{OS}/\Delta V_S)$  |.



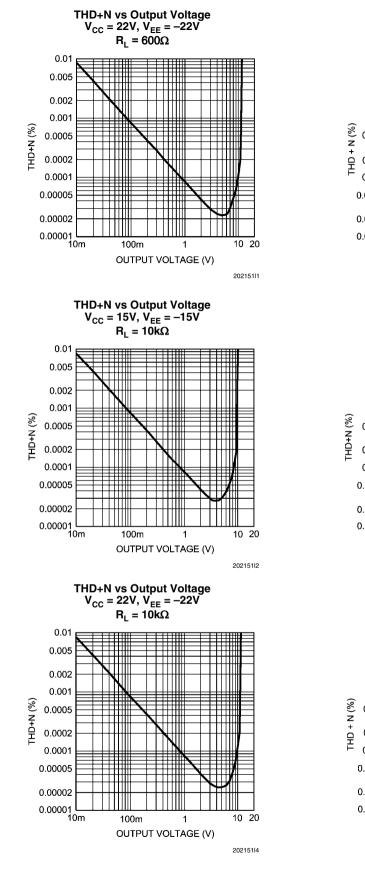


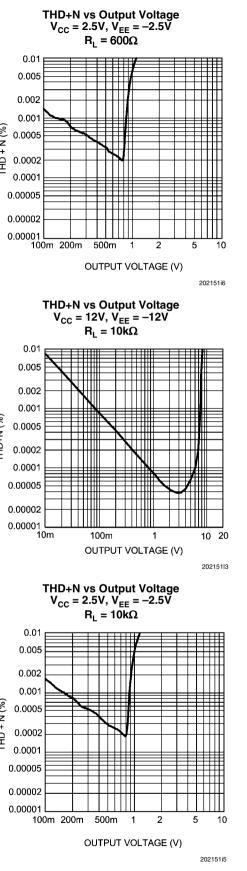


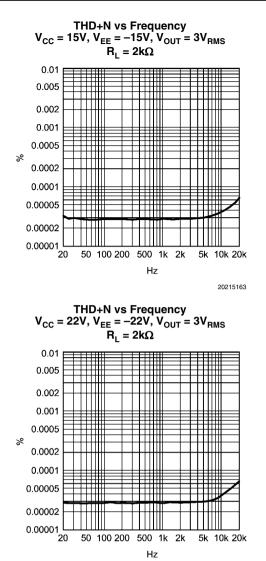
#### 5

202151k9

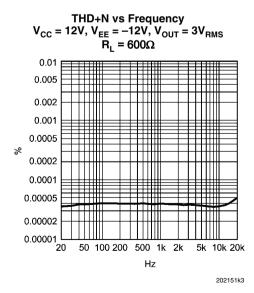


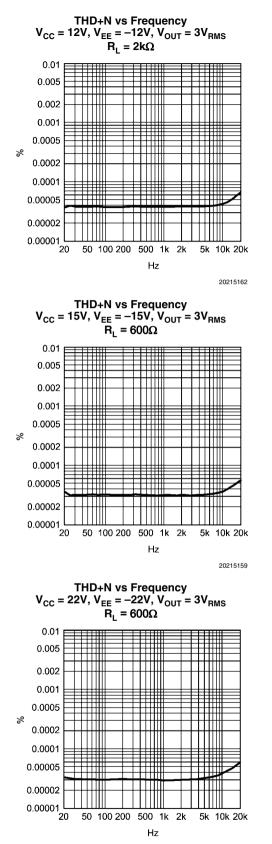






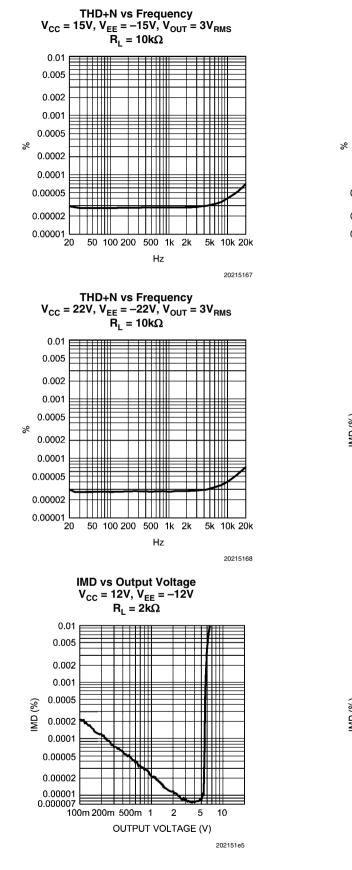
20215164

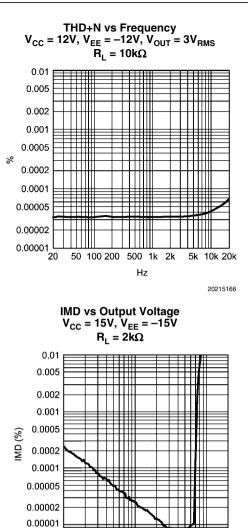




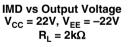
20215160







202151e6

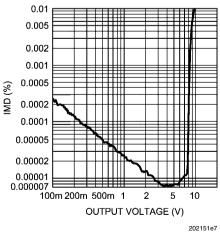


2 5 10

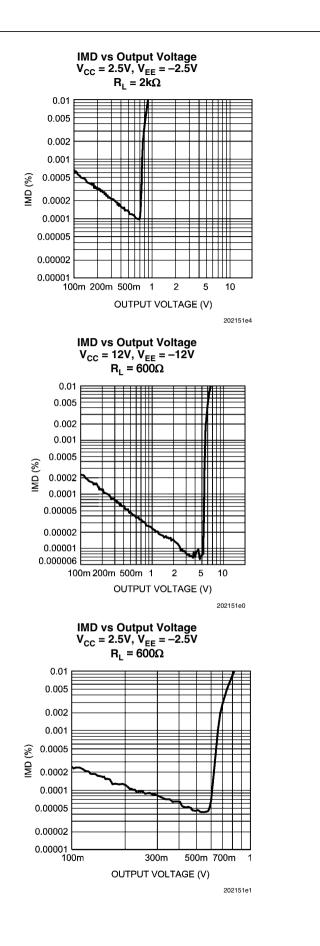
OUTPUT VOLTAGE (V)

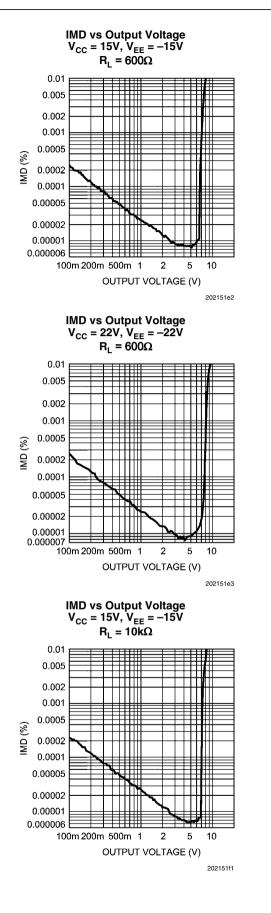
100m 200m 500m 1

0.000007

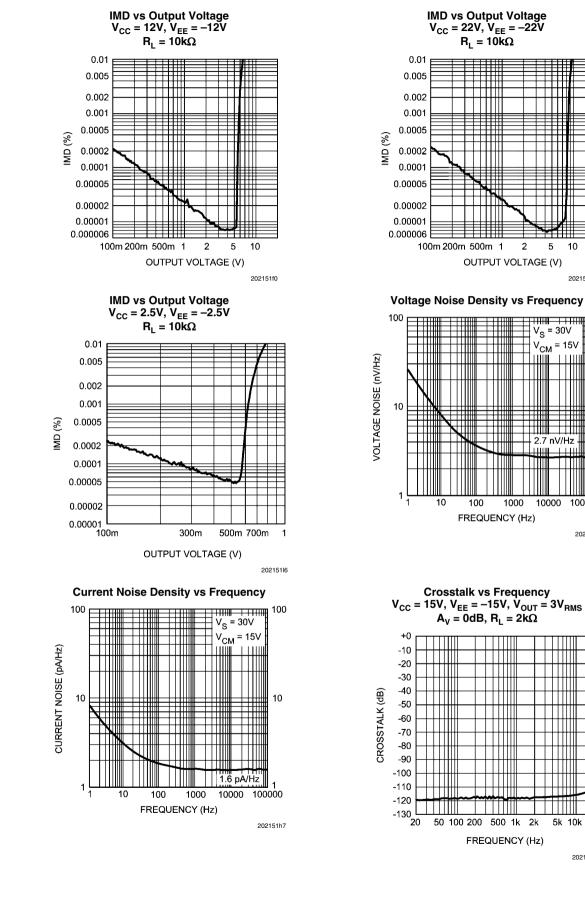


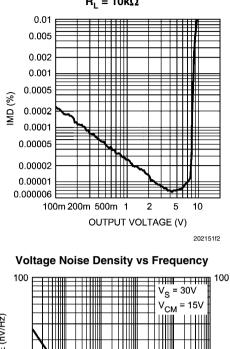












10

100000

202151h6

2.7 nV/Hz

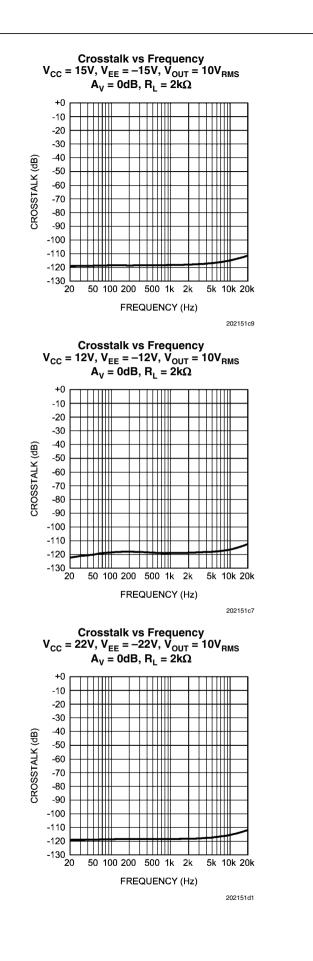
10000

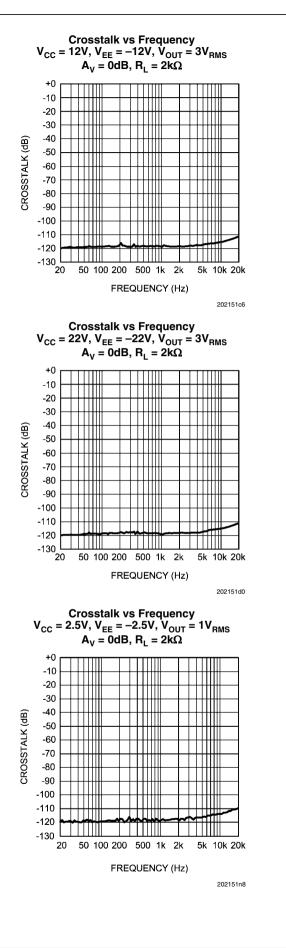
2k

5k 10k 20k

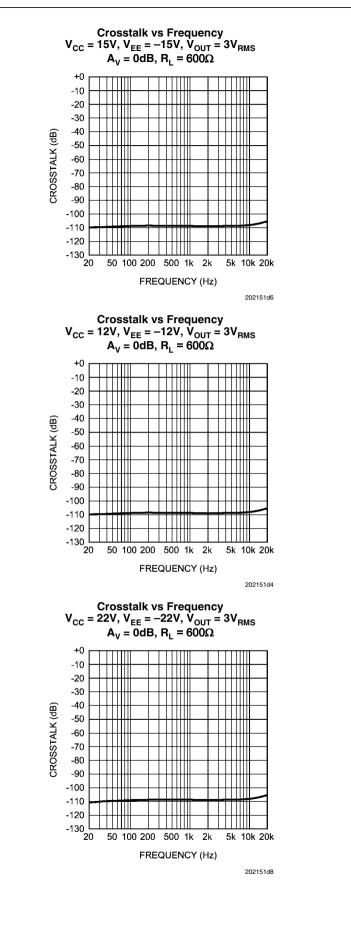
202151c8

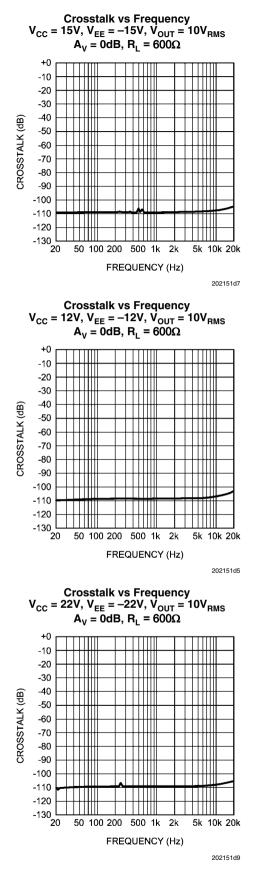
1000

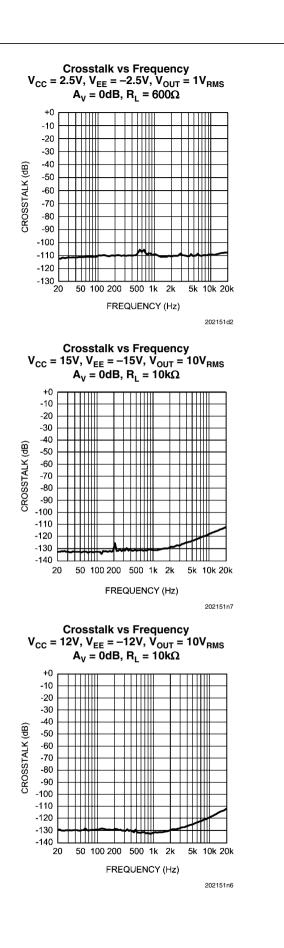


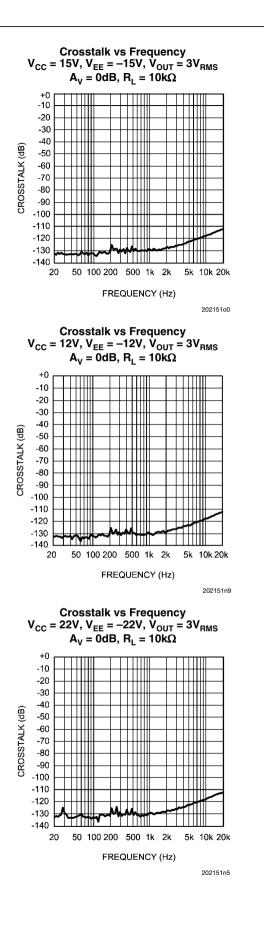


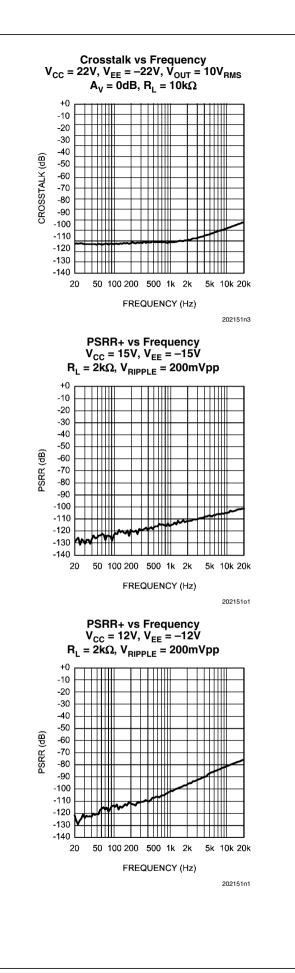


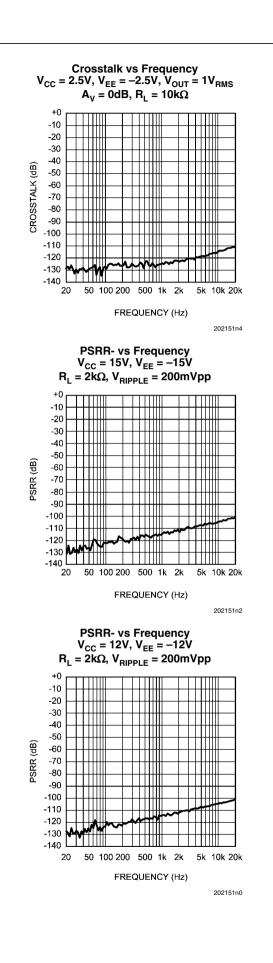


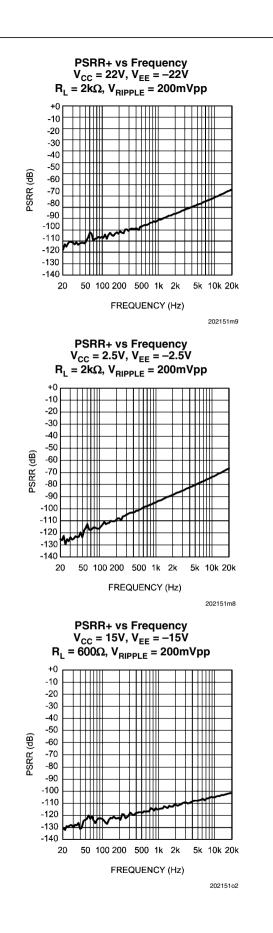


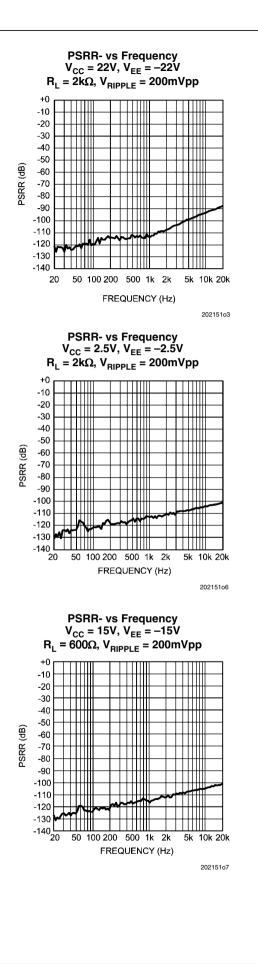


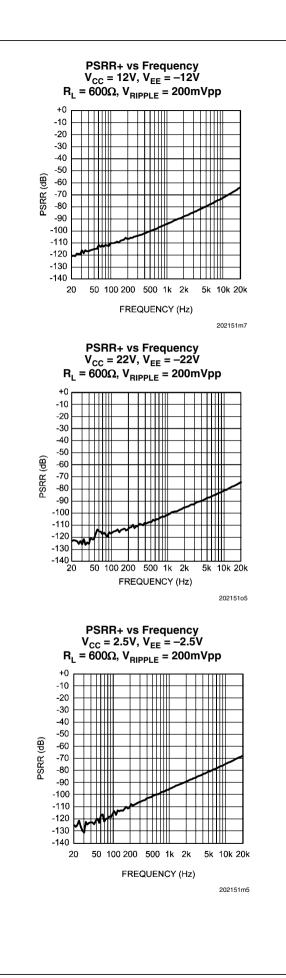


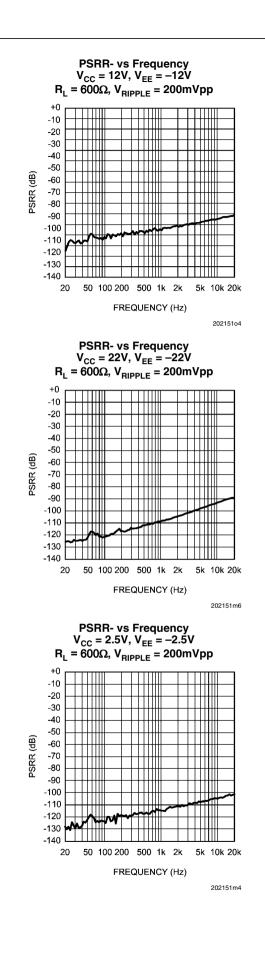












5k 10k 20k

5k 10k 20k

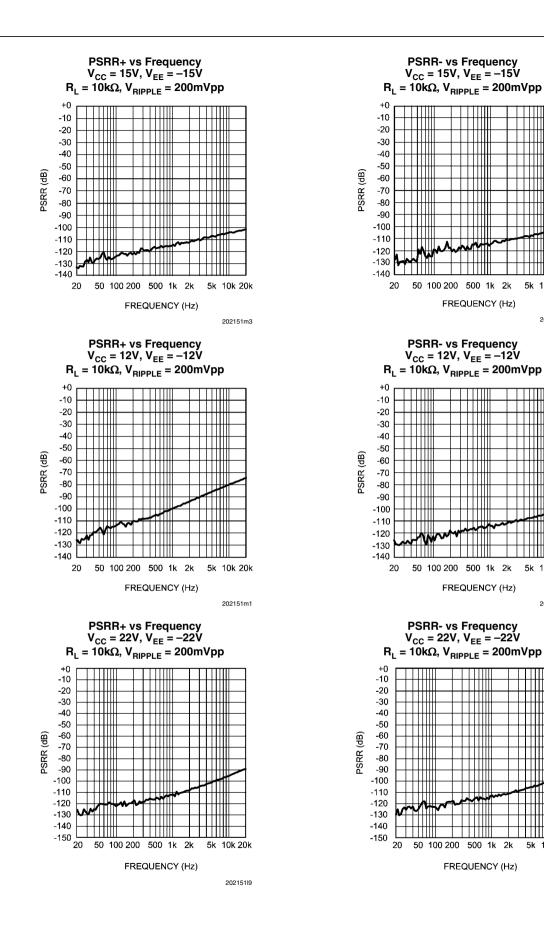
202151m0

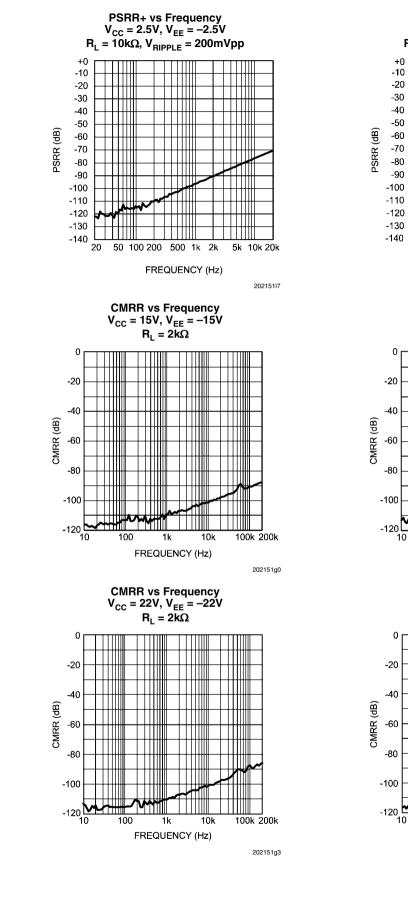
5k 10k 20k

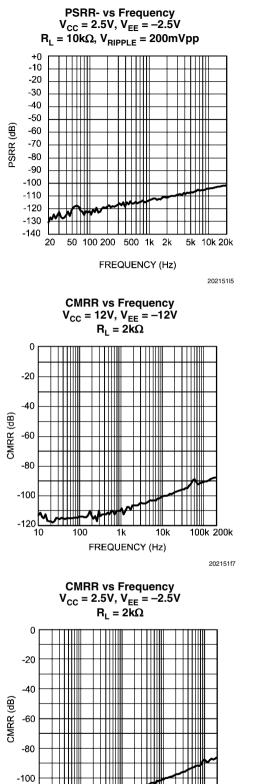
20215118

FREQUENCY (Hz)

202151m2







202151f4

100k 200k

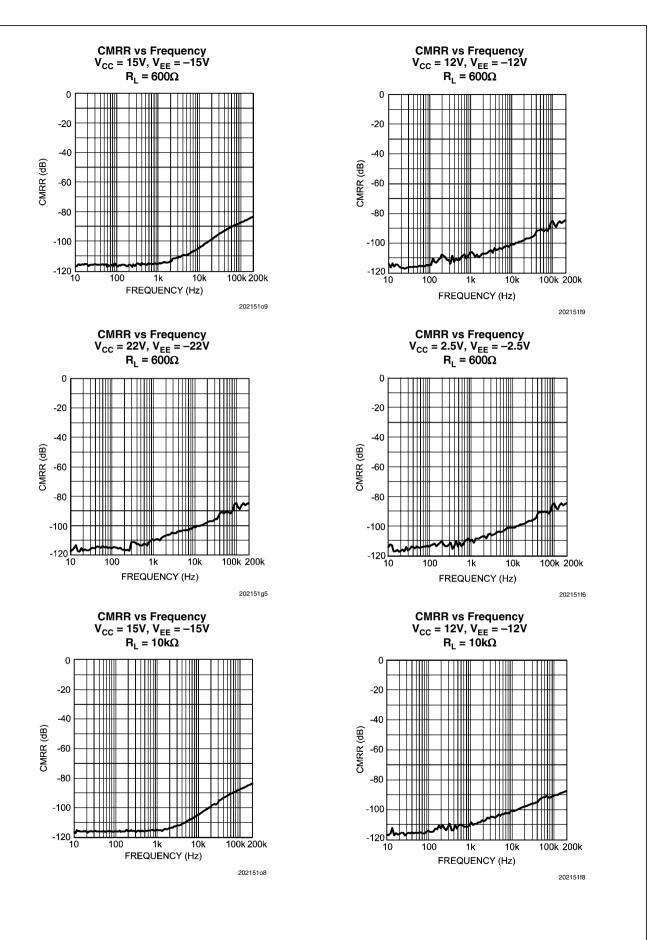
111

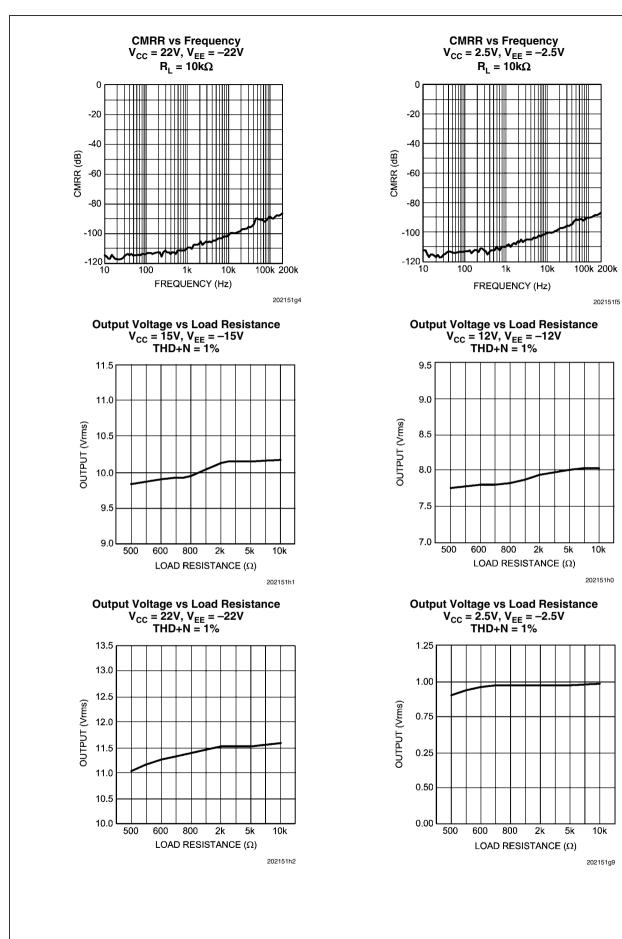
100

1k

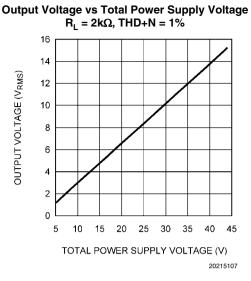
FREQUENCY (Hz)

10k

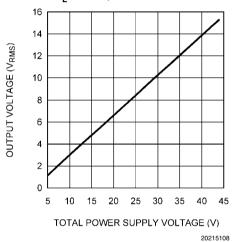




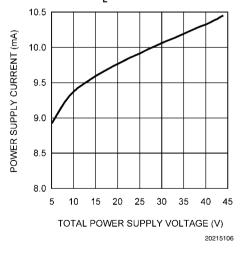
LME49860

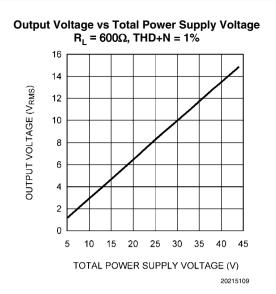


Output Voltage vs Total Power Supply Voltage  $R_i = 10k\Omega$ , THD+N = 1%

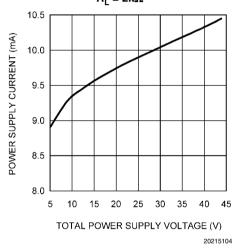


Power Supply Current vs Total Power Supply Voltage  $R_{\rm L}$  = 600  $\Omega$ 

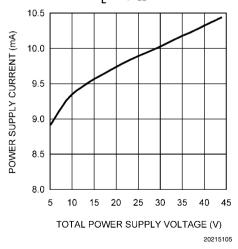




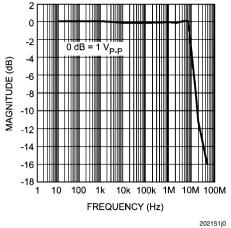
Power Supply Current vs Total Power Supply Voltage  $R_1 = 2k\Omega$ 

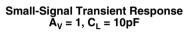


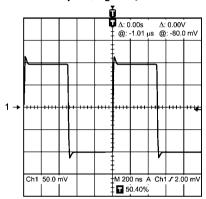
Power Supply Current vs Total Power Supply Voltage  $R_{L}$  = 10k $\Omega$ 



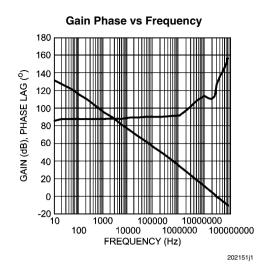
Full Power Bandwidth vs Frequency



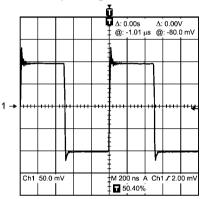








Small-Signal Transient Response  $A_V = 1, C_L = 100 pF$ 



202151i8

## **Application Information**

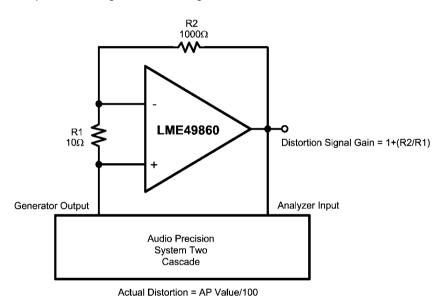
## DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LME49860 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution, however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49860's low residual distortion is an input referred internal error. As shown in Figure 1, adding the  $10\Omega$  resistor connected between the amplifier's inverting and non-inverting

inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101, which means that measurement resolution increases by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 1.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so produces distortion components that are within the measurement equipment's capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.



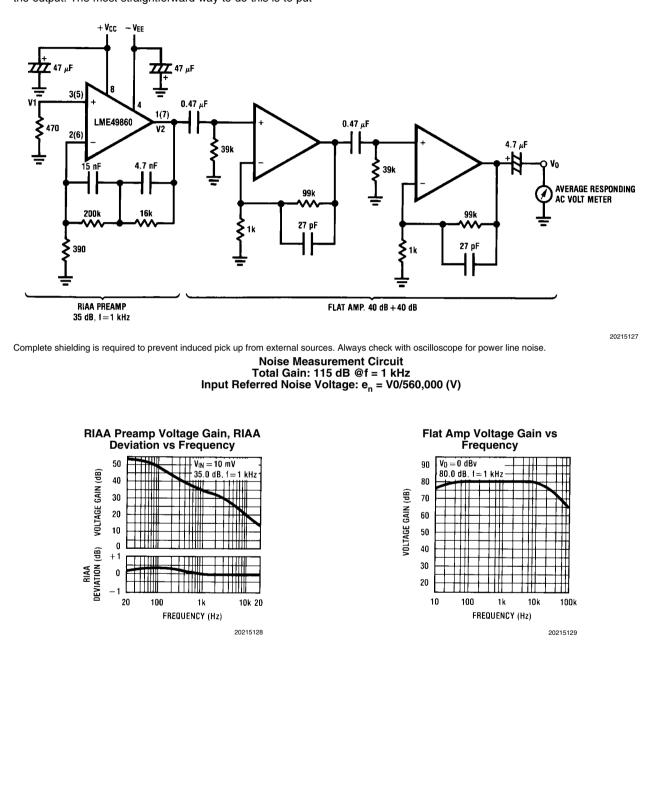
202151k4



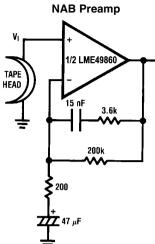
The LME49860 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 100pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted.

Capacitive loads greater than 100pF must be isolated from the output. The most straightforward way to do this is to put

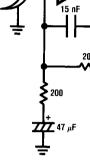


## **TYPICAL APPLICATIONS**



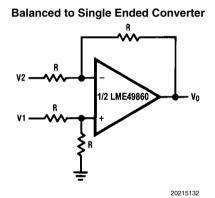
٧o

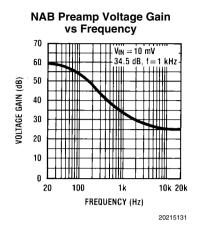
20215130





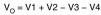
E<sub>n</sub> = 0.38 μV A Weighted



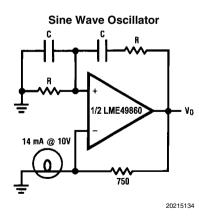


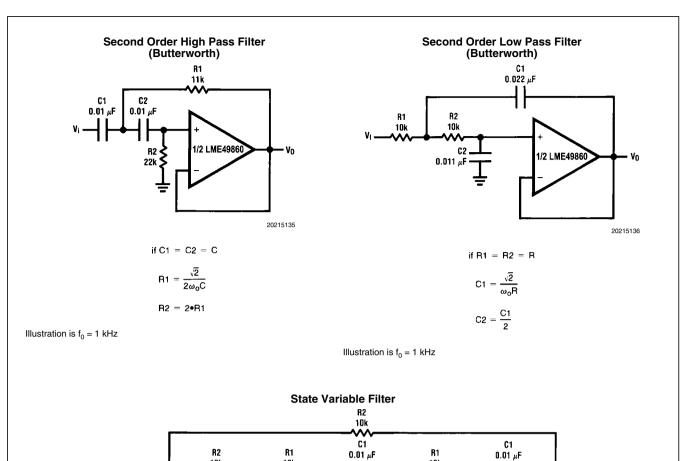
LME49860

Adder/Subtracter R V1 ٧2 1/2 LME49860 ٧o ₹₽ R R V۵ 20215133



 $V_0 = V1 - V2$ 





20215137

VLP

 $f_0 = \frac{1}{2\pi C1R1}, Q = \frac{1}{2}\left(1 + \frac{R2}{R0} + \frac{R2}{RG}\right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R2}{RG}$ 

1/2 LME49860

16k

VBP

븣

1/2 LME49860

16k

Vне

R2 =

 $\sim$ 

10k

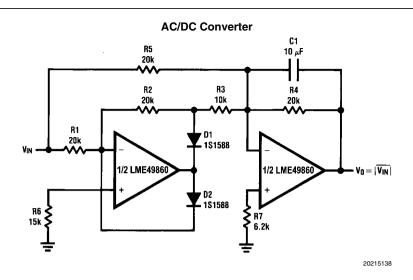
1/2 LME49860

Illustration is  $f_0 = 1$  kHz, Q = 10, A<sub>BP</sub> = 1

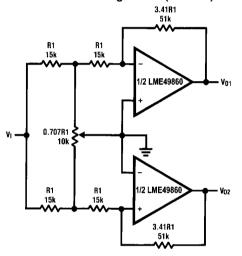
R<sub>G</sub> 10k

 $\sim$ 

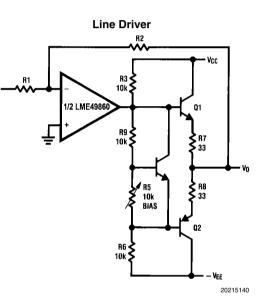
R0 556

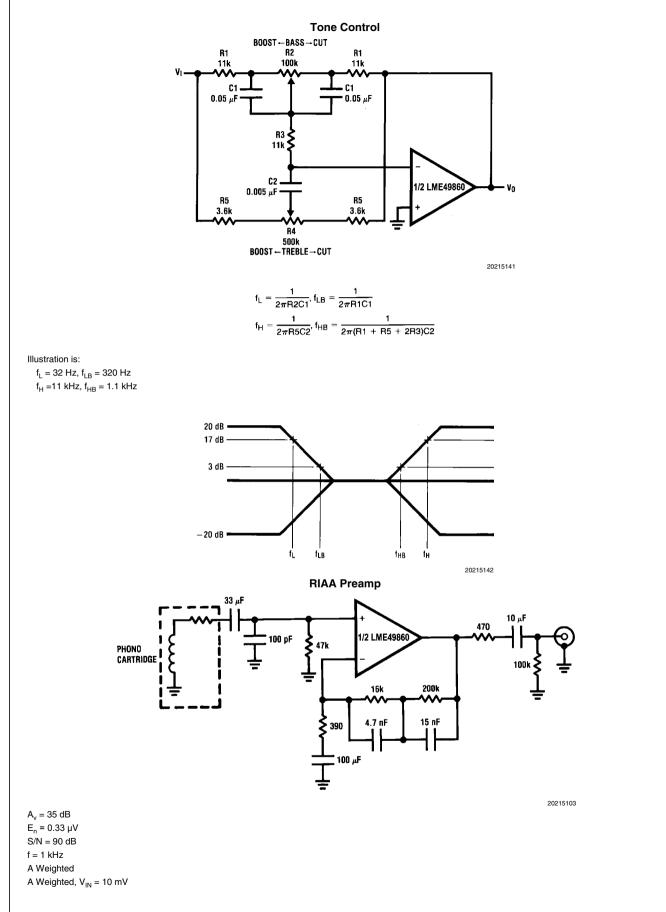


<sup>2</sup> Channel Panning Circuit (Pan Pot)

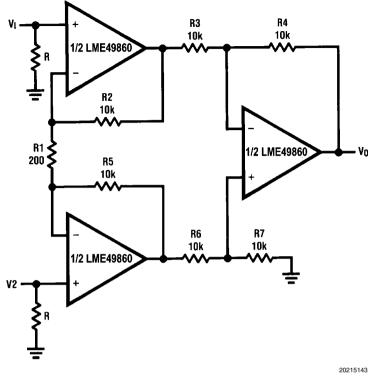






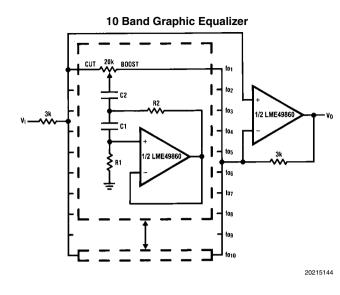






If R2 = R5, R3 = R6, R4 = R7 V0 =  $\left(1 + \frac{2R2}{R1}\right)\frac{R4}{R3}(V2 - V1)$ 

Illustration is: V0 = 101(V2 - V1)



fo (Hz)	<b>C</b> <sub>1</sub>	C <sub>2</sub>	R <sub>1</sub>	R <sub>2</sub>
32	0.12µF	4.7µF	75kΩ	500Ω
64	0.056µF	3.3µF	68kΩ	510Ω
125	0.033µF	1.5µF	62kΩ	510Ω
250	0.015µF	0.82µF	68kΩ	470Ω
500	8200pF	0.39µF	62kΩ	470Ω
1k	3900pF	0.22µF	68kΩ	470Ω
2k	2000pF	0.1µF	68kΩ	470Ω
4k	1100pF	0.056µF	62kΩ	470Ω
8k	510pF	0.022µF	68kΩ	510Ω
16k	330pF	0.012µF	51kΩ	510Ω

Note 9: At volume of change =  $\pm 12 \text{ dB}$ 

Q = 1.7

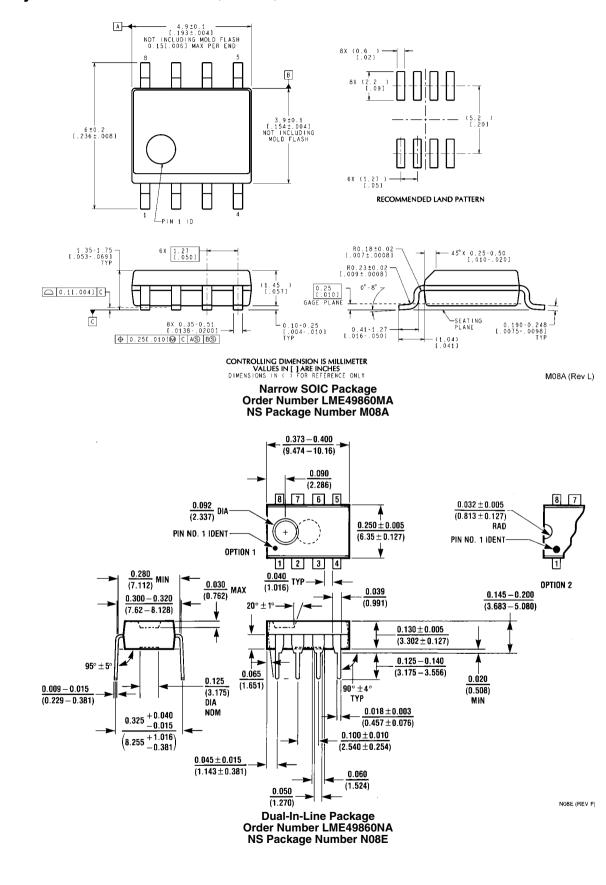
Reference: "AUDIO/RADIO HANDBOOK", National Semiconductor, 1980, Page 2-61

5
_
Ш
4
Ó
õ
σ
0

# **Revision History**

Rev	Date	Description
1.0	06/01/07	Initial release.
1.1	06/11/07	Added the LME49860MA and LME49860NA Top Mark Information.

## Physical Dimensions inches (millimeters) unless otherwise noted



# Notes

Notes

THE CONTENTS OF THIS DOCUMENT ARE PROVIDED IN CONNECTION WITH NATIONAL SEMICONDUCTOR CORPORATION ("NATIONAL") PRODUCTS. NATIONAL MAKES NO REPRESENTATIONS OR WARRANTIES WITH RESPECT TO THE ACCURACY OR COMPLETENESS OF THE CONTENTS OF THIS PUBLICATION AND RESERVES THE RIGHT TO MAKE CHANGES TO SPECIFICATIONS AND PRODUCT DESCRIPTIONS AT ANY TIME WITHOUT NOTICE. NO LICENSE, WHETHER EXPRESS, IMPLIED, ARISING BY ESTOPPEL OR OTHERWISE, TO ANY INTELLECTUAL PROPERTY RIGHTS IS GRANTED BY THIS DOCUMENT.

TESTING AND OTHER QUALITY CONTROLS ARE USED TO THE EXTENT NATIONAL DEEMS NECESSARY TO SUPPORT NATIONAL'S PRODUCT WARRANTY. EXCEPT WHERE MANDATED BY GOVERNMENT REQUIREMENTS, TESTING OF ALL PARAMETERS OF EACH PRODUCT IS NOT NECESSARILY PERFORMED. NATIONAL ASSUMES NO LIABILITY FOR APPLICATIONS ASSISTANCE OR BUYER PRODUCT DESIGN. BUYERS ARE RESPONSIBLE FOR THEIR PRODUCTS AND APPLICATIONS USING NATIONAL COMPONENTS. PRIOR TO USING OR DISTRIBUTING ANY PRODUCTS THAT INCLUDE NATIONAL COMPONENTS, BUYERS SHOULD PROVIDE ADEQUATE DESIGN, TESTING AND OPERATING SAFEGUARDS.

EXCEPT AS PROVIDED IN NATIONAL'S TERMS AND CONDITIONS OF SALE FOR SUCH PRODUCTS, NATIONAL ASSUMES NO LIABILITY WHATSOEVER, AND NATIONAL DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY RELATING TO THE SALE AND/OR USE OF NATIONAL PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

#### LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS PRIOR WRITTEN APPROVAL OF THE CHIEF EXECUTIVE OFFICER AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

Life support devices or systems are devices which (a) are intended for surgical implant into the body, or (b) support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in a significant injury to the user. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system or to affect its safety or effectiveness.

National Semiconductor and the National Semiconductor logo are registered trademarks of National Semiconductor Corporation. All other brand or product names may be trademarks or registered trademarks of their respective holders.

Copyright© 2007 National Semiconductor Corporation

For the most current product information visit us at www.national.com



National Semiconductor Americas Customer Support Center Email: new.feedback@nsc.com Tel: 1-800-272-9959 National Semiconductor Europe Customer Support Center Fax: +49 (0) 180-530-85-86 Email: europe.support@nsc.com Deutsch Tel: +49 (0) 69 9508 6208 English Tel: +49 (0) 870 24 0 2171 Français Tel: +33 (0) 1 41 91 8790 National Semiconductor Asia Pacific Customer Support Center Email: ap.support@nsc.com National Semiconductor Japan Customer Support Center Fax: 81-3-5639-7507 Email: jpn.feedback@nsc.com Tel: 81-3-5639-7560